Din-Tek SEMICONDUCTOR

DTS2305

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# P-Channel & V (D-S) MOSFET

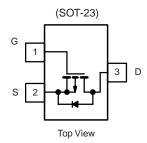
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 20			
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = - 4.5 V	0.058			
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = - 2.5 V	0.082			
$R_{DS(on)}(\Omega)$ at $V_{GS}$ = - 1.8 V	0.117			
I <sub>D</sub> (A)	- 5			
Configuration	Single			

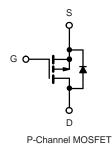
#### FEATURES

- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC

#### APPLICATIONS

Load Switch for Portable Devices





<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \text{ °C}$ , unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	- 20	V	
Gate-Source Voltage		V <sub>GS</sub>	± 8	v	
Continuous Drain Current	T <sub>C</sub> = 25 °C		- 5		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	- 3		
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	- 2.5	А	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	- 20		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 11		
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	6	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	PD	2	w	
	T <sub>C</sub> = 125 °C	۲D	0.67	vv	
Operating Junction and Storage Temperature Ran	ige	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	175	°C/W	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	75	0/10	

RoHS COMPLIANT

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = -250 \mu A$		- 20	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		- 0.45	-	- 2	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 12 V	-	-	- 1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS}$ = - 12 V, T <sub>J</sub> = 125 °C	-	-	- 50	μA
		$V_{GS} = 0 V$	$V_{DS}$ = - 12 V, T <sub>J</sub> = 175 °C	-	-	- 150	1
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = -4.5 V$	$V_{DS} \le$ - 5 V	- 10	-	-	Α
		$V_{GS} = -4.5 V$	I <sub>D</sub> = - 3.5 A	-	0.058	0.064	
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 3.5 A, T <sub>J</sub> = 125 °C	-	0.066	0.071	1
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 3.5 A, T <sub>J</sub> = 175 °C	-	0.075	0.079	Ω
		$V_{GS} = -2.5 V$	I <sub>D</sub> = - 3 A	-	0.082	0.091	1
		V <sub>GS</sub> = - 1.8 V	I <sub>D</sub> = - 2 A	-	0.117	0.129	1
Forward Transconductanceb	g <sub>fs</sub>	V <sub>DS</sub> =	- 5 V, I <sub>D</sub> = - 1.6 A	-	7	-	S
Dynamic <sup>b</sup>	·						
Input Capacitance	C <sub>iss</sub>		-	695	-		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 6 V, f = 1 MHz	-	265	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	190	-	
Total Gate Charge <sup>c</sup>	Qg				8.4		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 4.5 V	$V_{DS} = -6 V, I_{D} = -3.85 A$	-	1	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	2.4	-	
Gate Resistance	Rg	f = 1 MHz		4.1	8.2	12.3	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD}$ = - 6 V, R <sub>L</sub> = 1.6 Ω I <sub>D</sub> ≅ - 3.85 A, V <sub>GEN</sub> = - 4.5 V, R <sub>g</sub> = 1 Ω		-	17	-	
Rise Time <sup>c</sup>	t <sub>r</sub>			-	19	-	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	28	-	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	13	-	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 20	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	- 2 A, V <sub>GS</sub> = 0 V	-	- 0.8	- 1.2	V

#### Notes

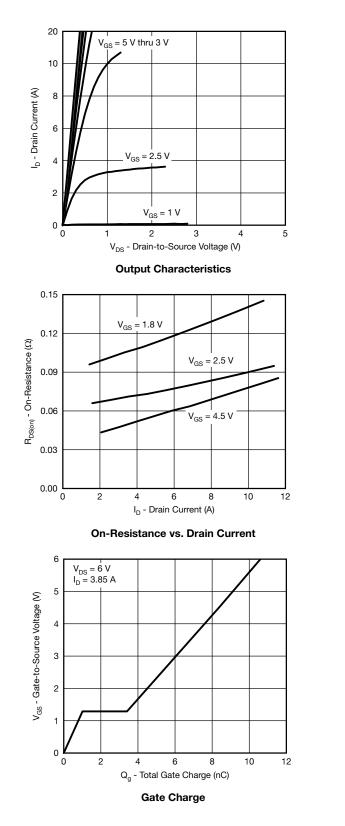
a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

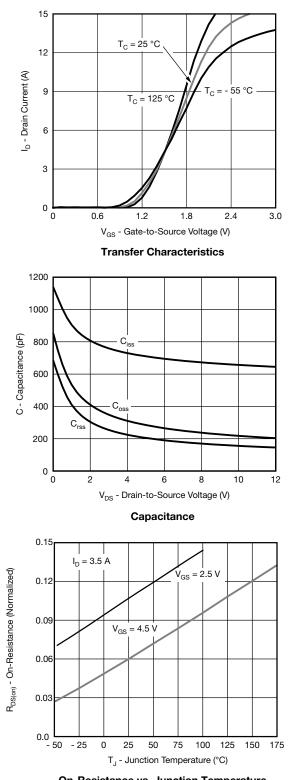
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





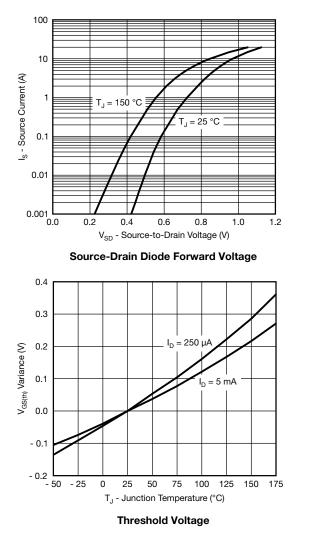
#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



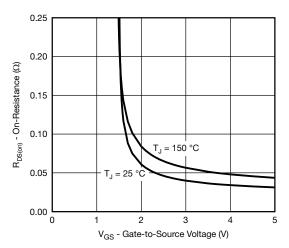
**On-Resistance vs. Junction Temperature** 



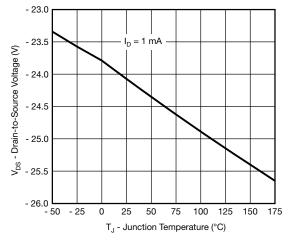
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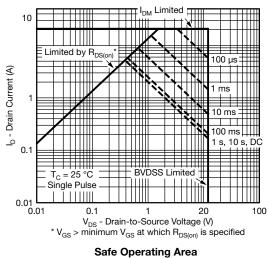
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



**On-Resistance vs. Gate-to-Source Voltage** 

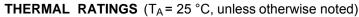


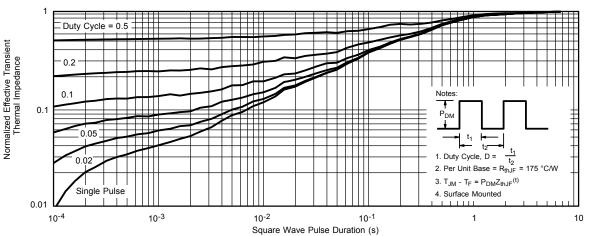
Drain Source Breakdown vs. Junction Temperature



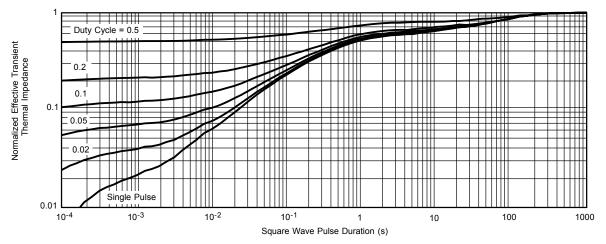


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Normalized Thermal Transient Impedance, Junction-to-Foot



Normalized Thermal Transient Impedance, Junction-to-Ambient

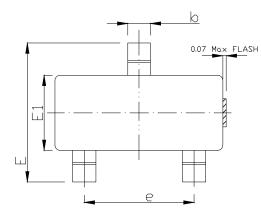
#### Note

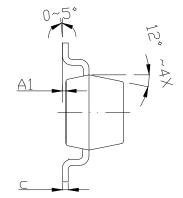
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 C)

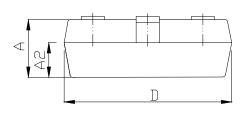
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

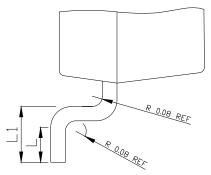


### SOT-23 PACKAGE OUTLINE









### COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

CVAIDOL	MILLIMETER			
SYMBOL	MIN	NOM	MAX	
А	0.80	1.00	1.30	
A1	0.00	0.05	0.15	
b	0.25	0.40	0.55	
С	0.11 BSC			
D	2 <b>. 6</b> 0	2.90	3 <b>. 2</b> 0	
Е	2.10	2.40	2.70	
E1	1.10	1.30	1.48	
е	1.90 BSC			
L	0.17	_	_	
L1	0.28	0.40	0.53	
A2	0.60 REF			



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